

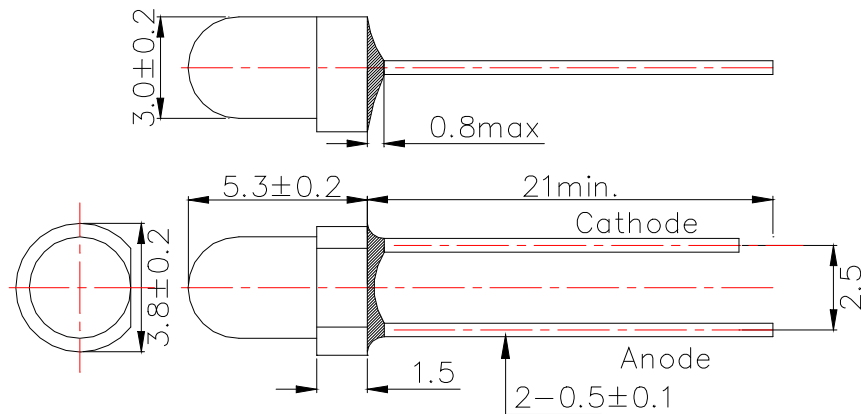
Data Sheet

L660N-34

High Bright Red LED Lamp

USHIO

Outline and Internal Circuit



(Unit : mm)

Features

- Chip Material : AlGaInP
- Chip Dimension : $350 \mu\text{m} * 350 \mu\text{m}$
- Number of Chips : 1pce
- Peak Wavelength : 660 nm typ.
- Package Type : $\phi 3 \text{ mm}$ clear molding
- Lead Frame : Soldered (Lead Free)
- Lens : Epoxy Resin

Application

Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Ratings	Unit
Power Dissipation	PD	120	mW
Forward Current	IF	50	mA
Pulse Forward Current	IFP	300	mA
Reverse Voltage	VR	5	V
Thermal Resistance	Rthja	160	K/W
Junction Temperature	Tj	120	°C
Operating Temperature	Topr	-40 ~ +100	°C
Storage Temperature	Tstg	-40 ~ +100	°C
Soldering Temperature	TSOL	265	°C

‡Pulse Forward Current condition : Duty 1% and Pulse Width=10us.

‡Soldering condition : Soldering condition must be completed with 3 seconds at 265°C.

Optical and Electrical Characteristics (Tc=25°C)

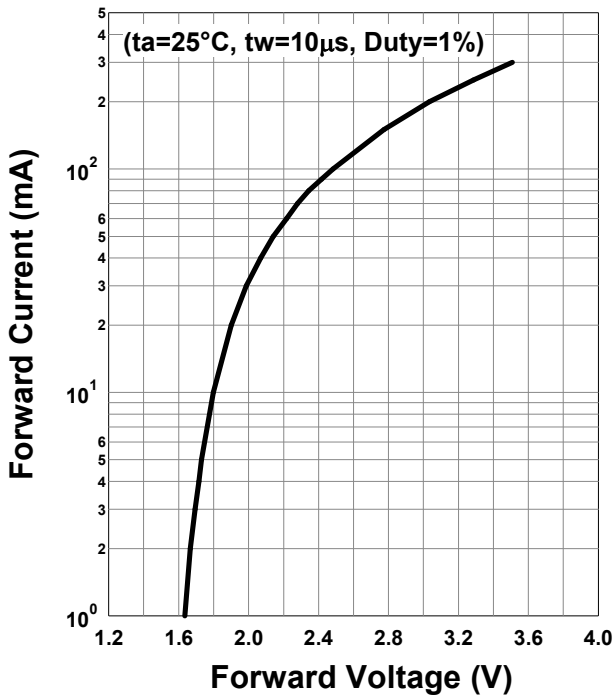
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Forward Voltage	VF		1.9	2.3	V	IF=20mA
	VFP		3.5			IFP=300mA
Total Radiated Power	PO	8	13		mW	IF=20mA
			170			IFP=300mA
Radiant Intensity	IE		66		mW/sr	IF=20mA
			860			IFP=300mA
Luminous Flux	ΦV		870		mlm	IF=20mA
Peak Wavelength	λp	650		670	nm	IF=20mA
Dominant Wavelength	λD		640		nm	IF=20mA
Half Width	Δλ		16		nm	IF=20mA
Viewing Half Angle	θ1/2		±8		deg.	IF=20mA
Rise Time	tr		10		ns	IF=20mA
Fall Time	tf		10		ns	IF=20mA

‡ Radiated Power is measured by S3584-08.

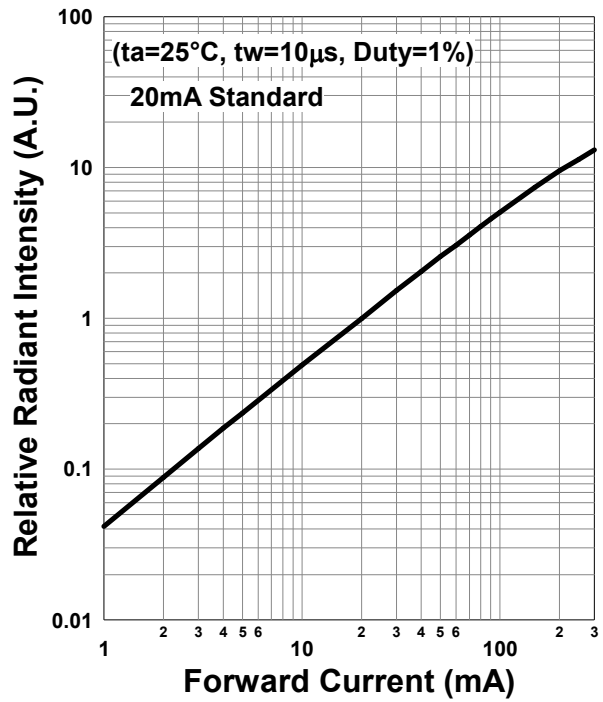
‡ Radiant Intensity is measured by CIE127-2007 Condition B.

Typical Characteristic Curves

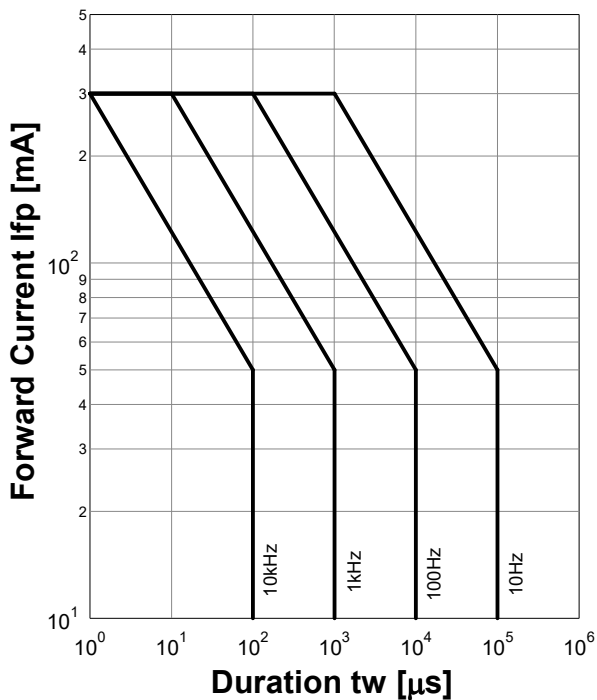
Forward Current - Forward Voltage



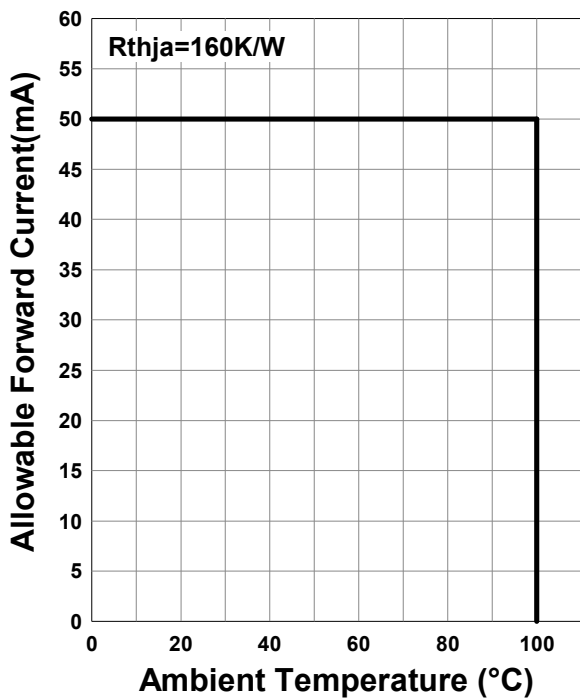
Relative Radiant Intensity - Forward Current



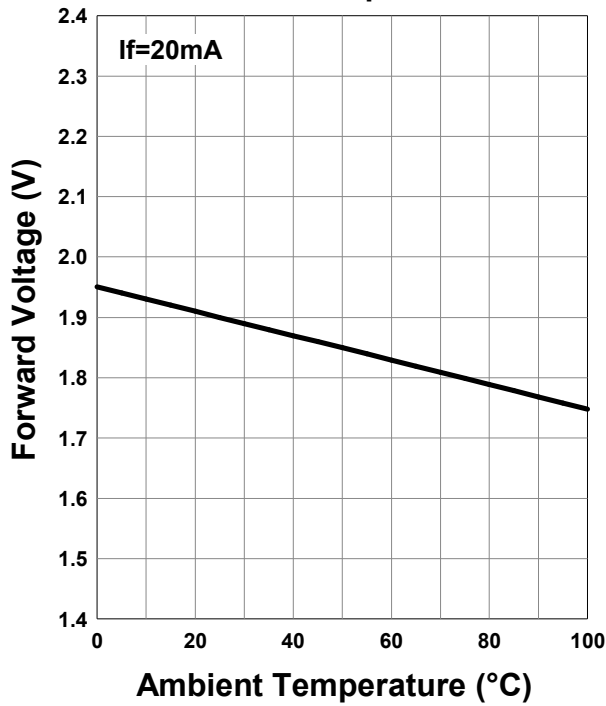
Forward Current - Pulse Duration



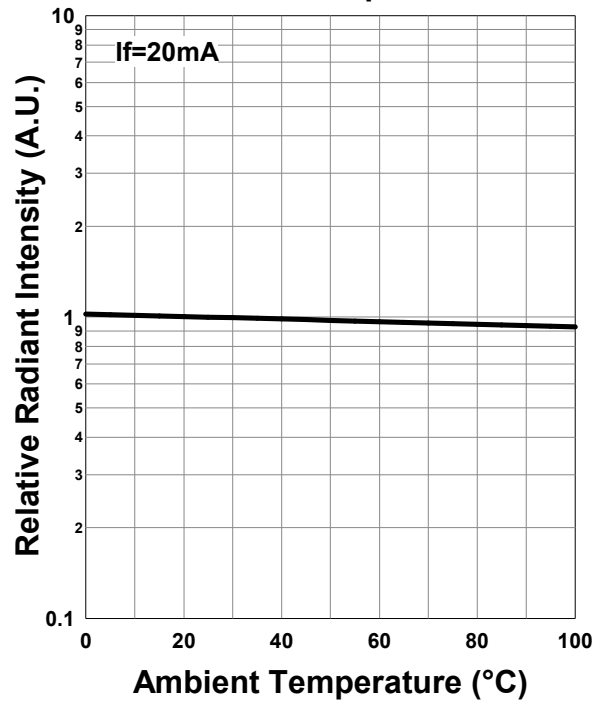
Allowable Forward Current - Ambient Temperature



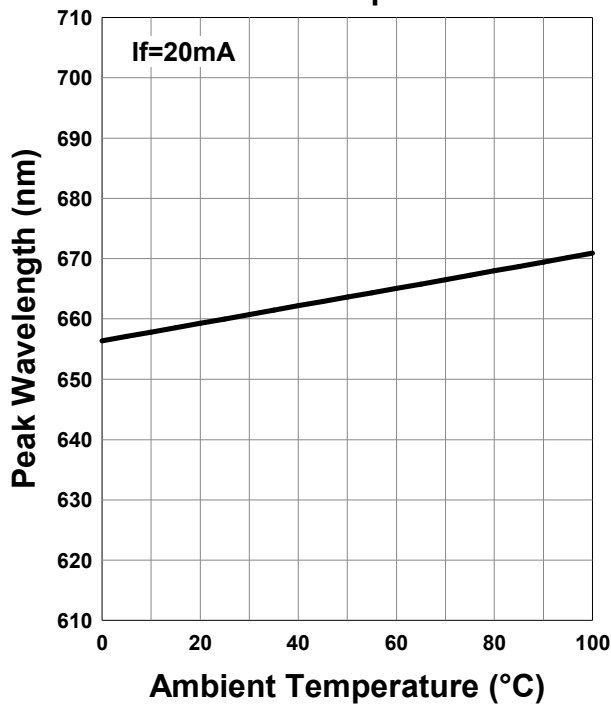
Forward Voltage - Ambient Temperature



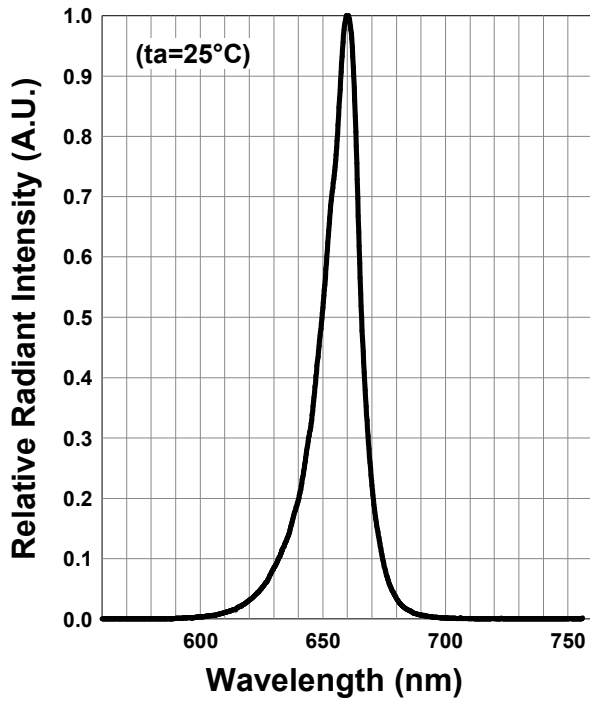
Relative Radiant Intensity - Ambient Temperature



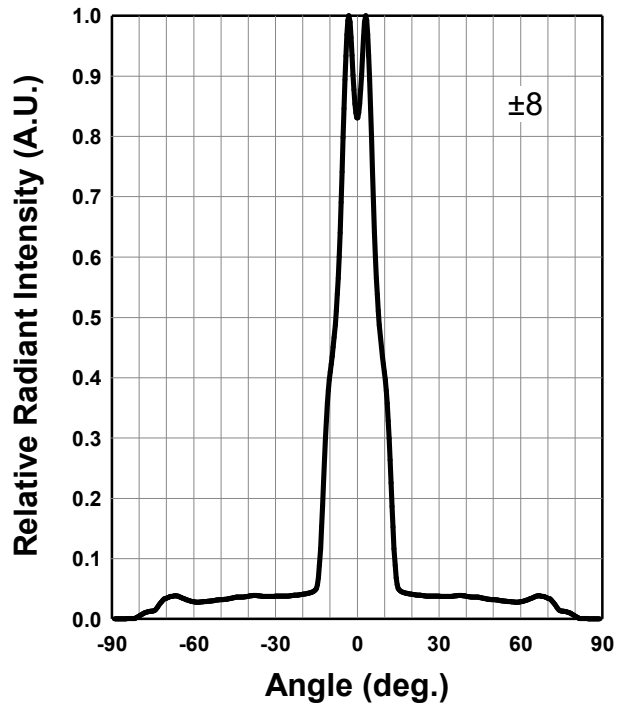
Peak Wavelength - Ambient Temperature



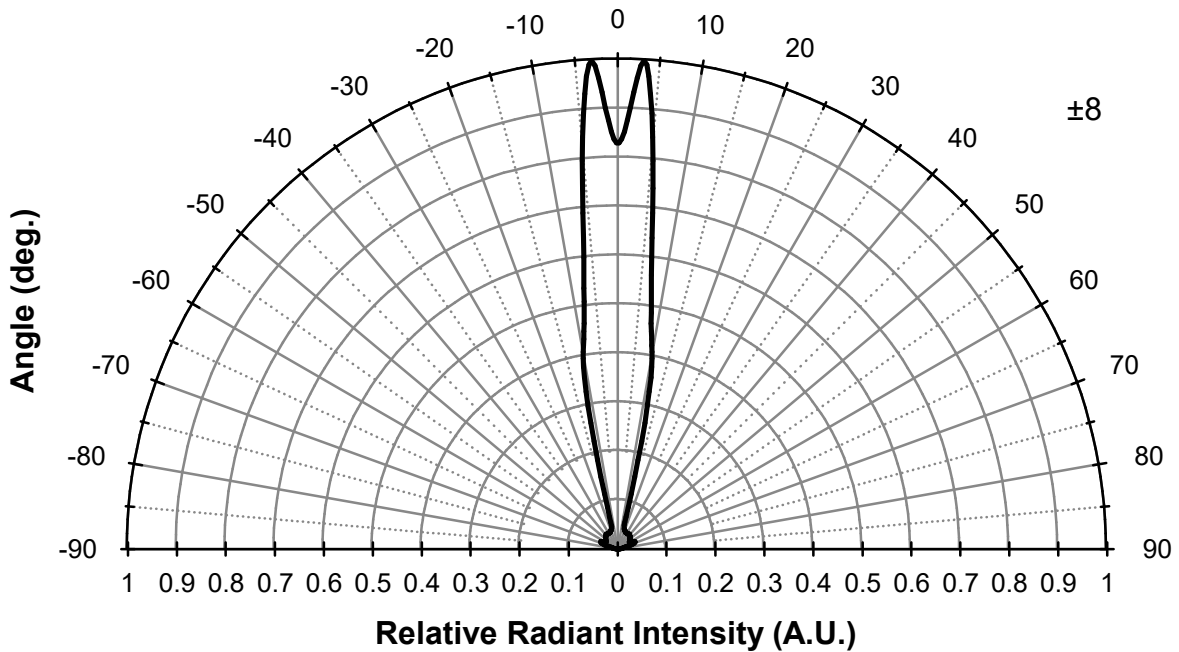
Relative Spectral Emission



Radiation Characteristics



Radiation Characteristics



Disclaimer

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Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

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*Effective July 2016, Ushio Epitex Inc. is now USHIO OPTO SEMICONDUCTORS, INC.